



ON Semiconductor®

# FDP18N50 / FDPF18N50 / FDPF18N50T

## N-Channel UniFET™ MOSFET

500 V, 18 A, 265 mΩ

### Features

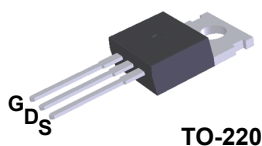
- $R_{DS(on)} = 220 \text{ m}\Omega$  (Typ.) @  $V_{GS} = 10 \text{ V}$ ,  $I_D = 9 \text{ A}$
- Low Gate Charge (Typ. 45 nC)
- Low  $C_{rss}$  (Typ. 25 pF)
- 100% Avalanche Tested

### Applications

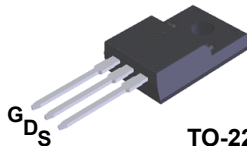
- LCD/LED/PDP TV
- Lighting
- Uninterruptible Power Supply

### Description

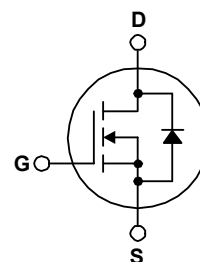
UniFET™ MOSFET is ON Semiconductor's high voltage MOSFET family based on planar stripe and DMOS technology. This MOSFET is tailored to reduce on-state resistance, and to provide better switching performance and higher avalanche energy strength. This device family is suitable for switching power converter applications such as power factor correction (PFC), flat panel display (FPD) TV power, ATX and electronic lamp ballasts.



TO-220



TO-220F



### Absolute Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter		FDP18N50	FDPF18N50 / FDPF18N50T	Unit
$V_{DSS}$	Drain-Source Voltage		500		V
$I_D$	Drain Current	- Continuous ( $T_C = 25^\circ\text{C}$ )	18	18 *	A
		- Continuous ( $T_C = 100^\circ\text{C}$ )	10.8	10.8 *	A
$I_{DM}$	Drain Current	- Pulsed (Note 1)	72	72 *	A
$V_{GSS}$	Gate-Source voltage		$\pm 30$		V
$E_{AS}$	Single Pulsed Avalanche Energy	(Note 2)	945		mJ
$I_{AR}$	Avalanche Current	(Note 1)	18		A
$E_{AR}$	Repetitive Avalanche Energy	(Note 1)	23.5		mJ
$dv/dt$	Peak Diode Recovery $dv/dt$	(Note 3)	4.5		V/ns
$P_D$	Power Dissipation	( $T_C = 25^\circ\text{C}$ )	235	38.5	W
		- Derate Above $25^\circ\text{C}$	1.88	0.3	W/ $^\circ\text{C}$
$T_J, T_{STG}$	Operating and Storage Temperature Range		-55 to +150		$^\circ\text{C}$
$T_L$	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds		300		$^\circ\text{C}$

\* Drain current limited by maximum junction temperature

### Thermal Characteristics

Symbol	Parameter	FDP18N50	FDPF18N50 / FDPF18N50T	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	0.53	3.3	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient, Max.	62.5	62.5	$^\circ\text{C/W}$

## Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FDP18N50	FDP18N50	TO-220	Tube	N/A	N/A	50 units
FDPF18N50	FDPF18N50	TO-220F	Tube	N/A	N/A	50 units
FDPF18N50T	FDPF18N50T	TO-220F	Tube	N/A	N/A	50 units

## Electrical Characteristics $T_C = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Conditions	Min.	Typ.	Max	Unit
Off Characteristics						
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> = 0 V, I <sub>D</sub> = 250 μA	500	--	--	V
ΔBV <sub>DSS</sub> / ΔT <sub>J</sub>	Breakdown Voltage Temperature Coefficient	I <sub>D</sub> = 250 μA, Referenced to 25°C	--	0.5	--	V/°C
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> = 500 V, V <sub>GS</sub> = 0 V V <sub>DS</sub> = 400 V, T <sub>C</sub> = 125°C	-- --	-- --	1 10	μA μA
I <sub>GSSF</sub>	Gate-Body Leakage Current, Forward	V <sub>GS</sub> = 30 V, V <sub>DS</sub> = 0 V	--	--	100	nA
I <sub>GSSR</sub>	Gate-Body Leakage Current, Reverse	V <sub>GS</sub> = -30 V, V <sub>DS</sub> = 0 V	--	--	-100	nA
On Characteristics						
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA	3.0	--	5.0	V
R <sub>DS(on)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 9 A	--	0.220	0.265	Ω
g <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> = 40 V, I <sub>D</sub> = 9 A	--	25	--	S
Dynamic Characteristics						
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> = 25 V, V <sub>GS</sub> = 0 V, f = 1 MHz	--	2200	2860	pF
C <sub>oss</sub>	Output Capacitance		--	330	430	pF
C <sub>rss</sub>	Reverse Transfer Capacitance		--	25	40	pF
Switching Characteristics						
t <sub>d(on)</sub>	Turn-On Delay Time	V <sub>DD</sub> = 250 V, I <sub>D</sub> = 18 A, V <sub>GS</sub> = 10 V, R <sub>G</sub> = 25 Ω	--	55	120	ns
t <sub>r</sub>	Turn-On Rise Time		--	165	340	ns
t <sub>d(off)</sub>	Turn-Off Delay Time		--	95	200	ns
t <sub>f</sub>	Turn-Off Fall Time		--	90	190	ns
Q <sub>g</sub>	Total Gate Charge	V <sub>DS</sub> = 400 V, I <sub>D</sub> = 18 A, V <sub>GS</sub> = 10 V	--	45	60	nC
Q <sub>gs</sub>	Gate-Source Charge		--	12.5	--	nC
Q <sub>gd</sub>	Gate-Drain Charge		--	19	--	nC
Drain-Source Diode Characteristics and Maximum Ratings						
I <sub>S</sub>	Maximum Continuous Drain-Source Diode Forward Current		--	--	18	A
I <sub>SM</sub>	Maximum Pulsed Drain-Source Diode Forward Current		--	--	72	A
V <sub>SD</sub>	Drain-Source Diode Forward Voltage	V <sub>GS</sub> = 0 V, I <sub>S</sub> = 18 A	--	--	1.4	V
t <sub>rr</sub>	Reverse Recovery Time	V <sub>GS</sub> = 0 V, I <sub>S</sub> = 18 A, dI <sub>F</sub> /dt =100 A/μs	--	500	--	ns
Q <sub>rr</sub>	Reverse Recovery Charge		--	5.4	--	μC

### Notes:

1. Repetitive rating: pulse-width limited by maximum junction temperature.
2.  $L = 5.2\text{ mH}$ ,  $I_{AS} = 18\text{ A}$ ,  $V_{DD} = 50\text{ V}$ ,  $R_G = 25\text{ }\Omega$ , starting  $T_J = 25^\circ\text{C}$ .
3.  $I_{SD} \leq 18\text{ A}$ ,  $di/dt \leq 200\text{ A}/\mu\text{s}$ ,  $V_{DD} \leq BV_{DSS}$ , starting  $T_J = 25^\circ\text{C}$ .
4. Essentially independent of operating temperature typical characteristics.

## Typical Performance Characteristics

Figure 1. On-Region Characteristics

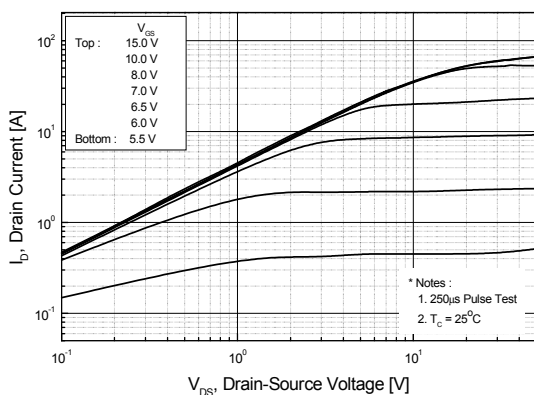


Figure 2. Transfer Characteristics

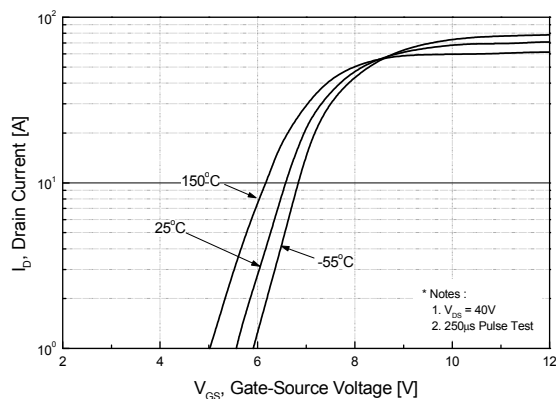


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

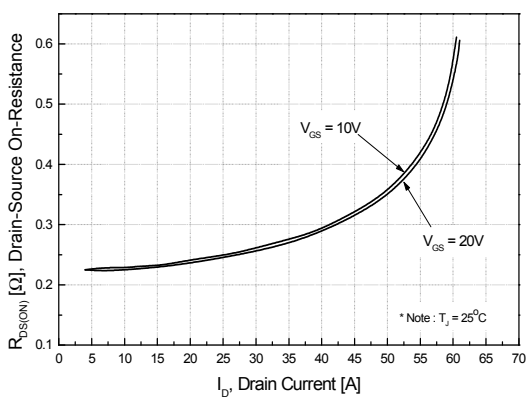


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

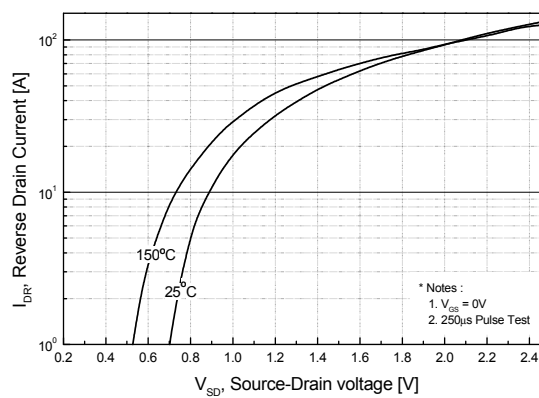


Figure 5. Capacitance Characteristics

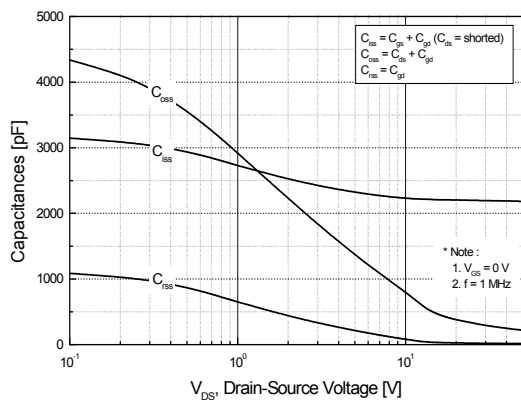
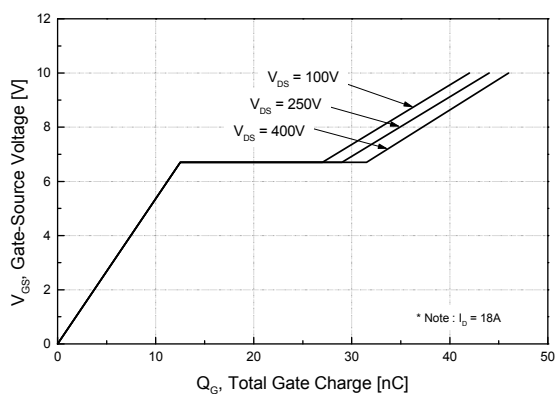
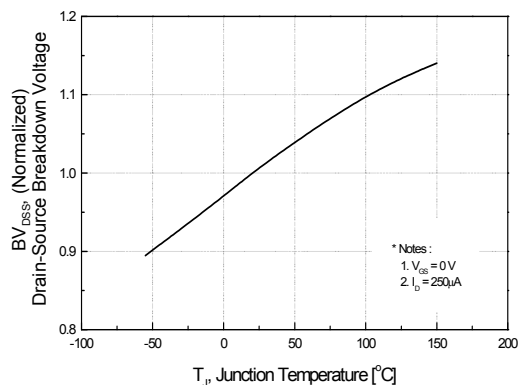


Figure 6. Gate Charge Characteristics

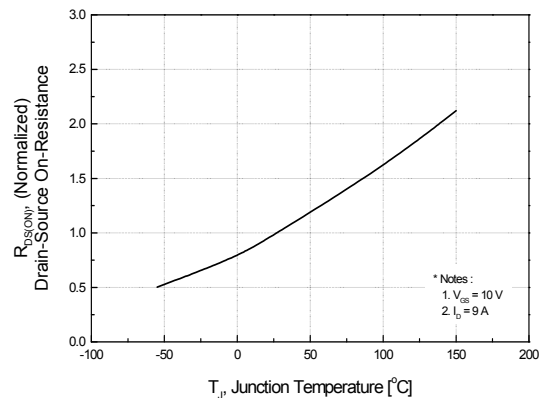


# Typical Performance Characteristics (Continued)

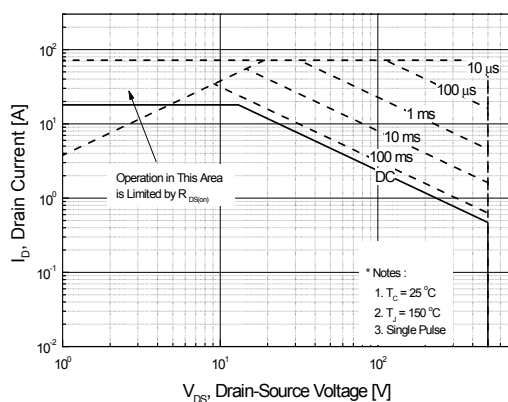
**Figure 7. Breakdown Voltage Variation vs. Temperature**



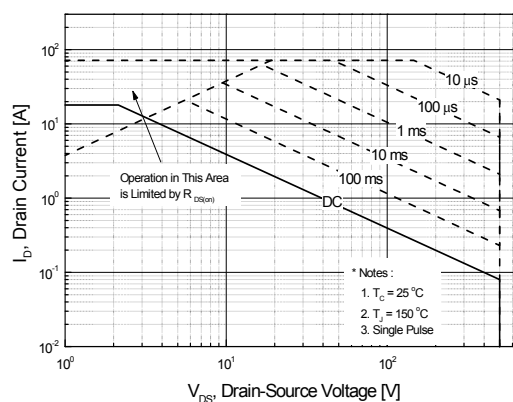
**Figure 8. On-Resistance Variation vs. Temperature**



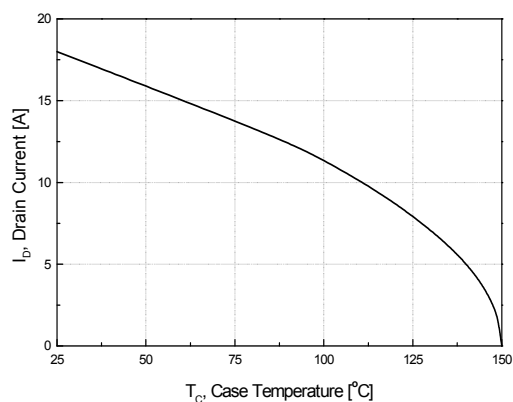
**Figure 9-1. Maximum Safe Operating Area - FDP18N50**



**Figure 9-2. Maximum Safe Operating Area - FDPF18N50 / FDPF18N50T**



**Figure 10. Maximum Drain Current vs. Case Temperature**



## Typical Performance Characteristics (Continued)

Figure 11-1. Transient Thermal Response Curve - FDP18N50

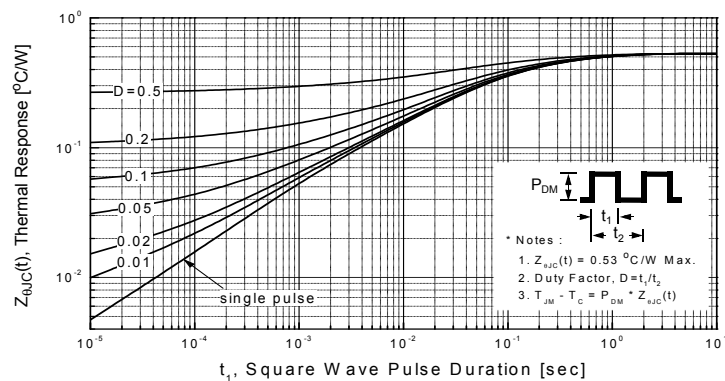
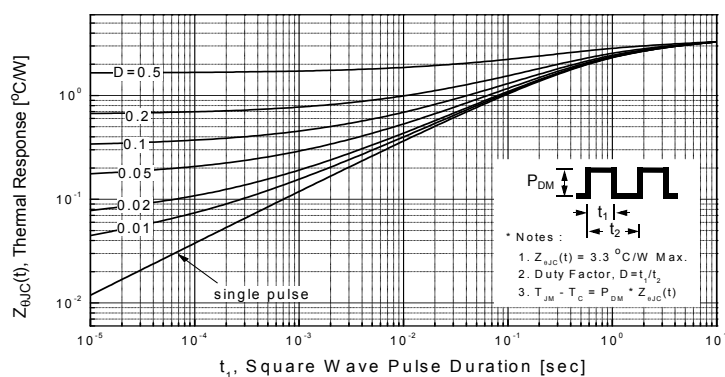


Figure 11-2. Transient Thermal Response Curve - FDPF18N50 / FDPF18N50T



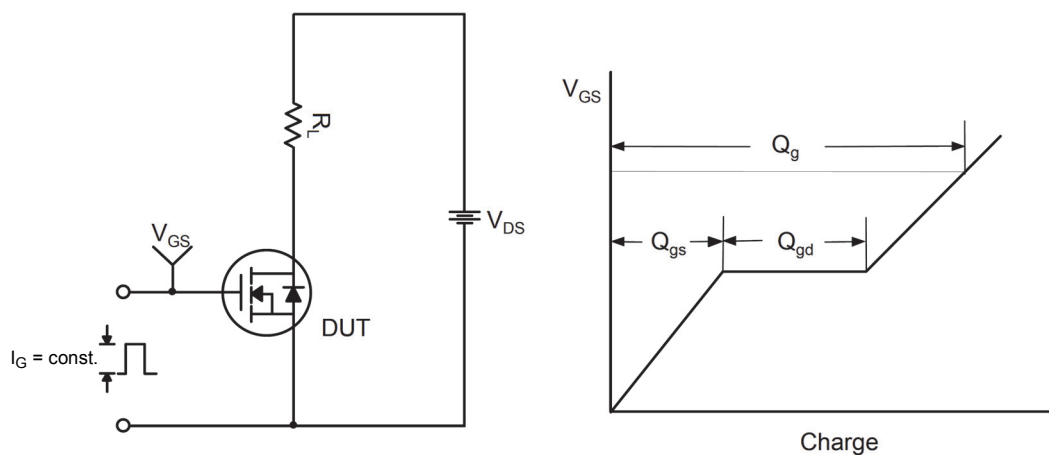


Figure 12. Gate Charge Test Circuit & Waveform

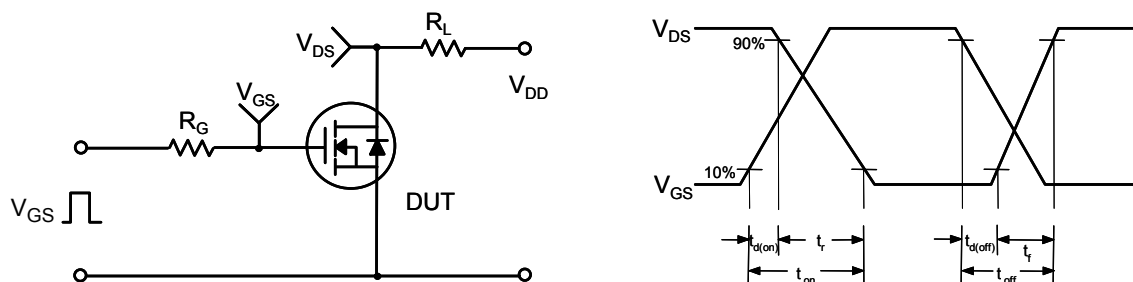


Figure 13. Resistive Switching Test Circuit & Waveforms



Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

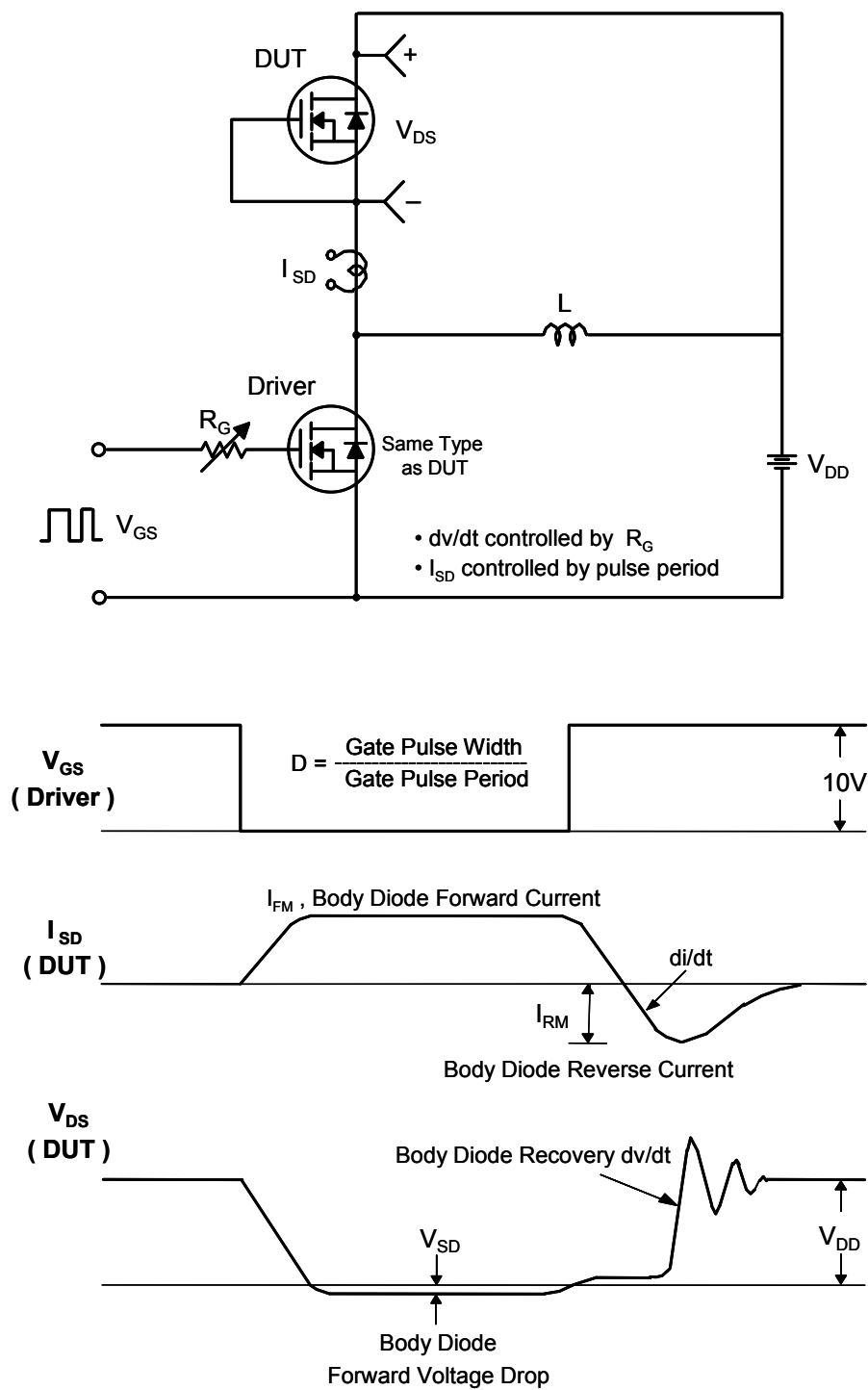
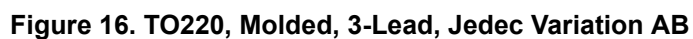



Figure 15. Peak Diode Recovery  $dv/dt$  Test Circuit & Waveforms

Downloaded from [Arrow.com](http://Arrow.com).





Downloaded from Arrow.com.

ON Semiconductor and  are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at [www.onsemi.com/site/pdf/Patent-Marking.pdf](http://www.onsemi.com/site/pdf/Patent-Marking.pdf). ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and hold ON Semiconductor and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that ON Semiconductor was negligent regarding the design or manufacture of the part. ON Semiconductor is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

## PUBLICATION ORDERING INFORMATION

### LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor  
19521 E. 32nd Pkwy, Aurora, Colorado 80011 USA  
**Phone:** 303-675-2175 or 800-344-3860 Toll Free USA/Canada  
**Fax:** 303-675-2176 or 800-344-3867 Toll Free USA/Canada  
**Email:** [orderlit@onsemi.com](mailto:orderlit@onsemi.com)

**N. American Technical Support:** 800-282-9855 Toll Free  
USA/Canada

**Europe, Middle East and Africa Technical Support:**  
Phone: 421 33 790 2910

**Japan Customer Focus Center**  
Phone: 81-3-5817-1050

**ON Semiconductor Website:** [www.onsemi.com](http://www.onsemi.com)

**Order Literature:** <http://www.onsemi.com/orderlit>

For additional information, please contact your local  
Sales Representative